[0/657,49, CA REG. E. L. STruc. search, 3/21/06, RAX
FORMULE CLI

RE.CNT 6 THERE ARE 6 CITED REFERENCES AVAILABLE FOR THIS RECORD ALL CITATIONS AVAILABLE IN THE RE FORMAT

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=> d his
     (FILE 'HOME' ENTERED AT 14:18:50 ON 21 MAR 2006)
     FILE 'REGISTRY' ENTERED AT 14:19:01 ON 21 MAR 2006
                STRUCTURE UPLOADED
L1
L2
                STRUCTURE UPLOADED
L3
           3125 S L1 FULL
L4
          18776 S L2 FULL
     FILE 'CAPLUS' ENTERED AT 14:21:48 ON 21 MAR 2006
            362 S L3
L5
L6
           1433 S L4
L7
          42960 S PHOTORESIST OR RESIST COMPOSITION
L8
              1 S L5 AND L7
L9
              5 S L6 AND L7
=> d l9 1-5 bib ab hitstr
L9
     ANSWER 1 OF 5 CAPLUS COPYRIGHT 2006 ACS on STN
     2004:963502 CAPLUS
AN
     141:417925
DN
     Positive-working vacuum-UV photoresist composition and
TI
     patterning method using the same
     Sasaki, Tomoya
IN
     Fuji Photo Film Co., Ltd., Japan
PA
     Jpn. Kokai Tokkyo Koho, 99 pp.
SO
     CODEN: JKXXAF
DT
     Patent
LA
     Japanese
FAN.CNT 1
     PATENT NO.
                    KIND
                               DATE
                                     APPLICATION NO.
                                                                   DATE
                                           JP 2003-293188
PΙ
     JP 2004318046
                         A2
                                20041111
                                                                   20030813
PRAI JP 2003-94329
                         Α
                                20030331
    Disclosed is the pos.-working vacuum-UV photoresist composition especially
     suited for a F2 excimer laser (157 nm) comprising (a) a resin having a
     repeating unit FROC-CFR1, FROC-CF(OR2), and/or F(R3O)C-CFR4 (R0,1 = H, F,
     alkyl, cycloalkyl, etc.; R2-4 = alkyl, cycloalkyl, etc.), and (b) a
    photoacid.
     791853-95-7
IT
    RL: PRP (Properties); TEM (Technical or engineered material use); USES
     (Uses)
        (pos.-working vacuum-UV photoresist composition containing
       fluoropolymer and photoacid)
RN
     791853-95-7 CAPLUS
    2-Propenoic acid, 5(or 6)-[3,3,3-trifluoro-2-(methoxymethoxy)-2-
CN
     (trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-yl ester, polymer with
    N-[5,6-bis(hydroxymethyl)bicyclo[2.2.1]hept-2-yl]-2-fluoro-2-propenamide
     and tetrafluoroethene (9CI) (CA INDEX NAME)
    CM
          1
```

CRN 791853-94-6

IDS

CCI

CMF C16 H20 F6 O4

CM 2

CRN 791853-93-5 CMF C12 H18 F N O3

$$\begin{array}{c|c} & \text{H}_2\text{C} & \text{O} \\ & & \text{II} & \text{II} \\ & & \text{C} & \text{C} - \text{C} - \text{NH} \\ & & \text{C} & \text{H}_2 - \text{OH} \\ & & \text{C} & \text{H}_2 - \text{OH} \\ \end{array}$$

R14 & Mikene (or dikenyland)

CM 3

CRN 116-14-3 CMF C2 F4

L9 ANSWER 2 OF 5 CAPLUS COPYRIGHT 2006 ACS on STN

AN 2004:801603 CAPLUS

DN 141:304291

TI Positive **photoresist** compositions showing high transparency to 157-nm F2 excimer lasers and forming patterns with small line-edge roughness and less scums

IN Kanda, Hiromi; Mizutani, Kazuyoshi; Kanna, Shinichi

PA Fuji Photo Film Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 68 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

PATENT NO. KIND DATE APPLICATION NO. DATE

PI JP 2004271630 A2 20040930 JP 2003-58733 20030305

PRAI JP 2003-58733 20030305

AB The compns. comprise (A) resins having (A1) [R1R2CCR3(OR4)] units [R1-R3 = H, (fluoro)alkyl, F; R4 = H, (fluoro)alkyl, L1X; X = polar group, alkaline

developer-soluble group, group solubilized in alkaline developers by acids; L1

single bond, divalent linking group] and (A2) [R5R6CCR7(CONR8R9)] units [R5-R7 = same as R1; R8, R9 = H, (fluoro)alkyl, L2Y; Y = same as X; L2 = same as L1] and (B) compds. generating acids by (actinic ray) radiation. 762301-12-2P

RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT

(Reactant or reagent)

(monomers; pos. photoresist compns. showing high transparency to F2 excimer lasers and forming patterns with small line-edge roughness and less scums)

RN 762301-12-2 CAPLUS

=

IT

CN

2-Propenamide, N-[6-[3,3,3-trifluoro-2-hydroxy-2-(trifluoromethyl)propyl]bicyclo[2.2.1]hept-2-yl]-2-(trifluoromethyl)-(9CI) (CA INDEX NAME)

$$H_2C$$
 O OH  $CH_2-C-CF_3$   $CF_3$ 

IT 762301-13-3P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(pos. photoresist compns. showing high transparency to F2 excimer lasers and forming patterns with small line-edge roughness and less scums)

RN 762301-13-3 CAPLUS

CN Bicyclo[2.2.1]heptane-2-carboxylic acid, 6-(ethenyloxy)-2(trifluoromethyl)-, 1,1-dimethylethyl ester, polymer with
N-[6-[3,3,3-trifluoro-2-hydroxy-2-(trifluoromethyl)propyl]bicyclo[2.2.1]he
pt-2-yl]-2-(trifluoromethyl)-2-propenamide (9CI) (CA INDEX NAME)

CM 1

CRN 762301-12-2 CMF C15 H16 F9 N O2

CM 2

CRN 634920-64-2 CMF C15 H21 F3 O3

$$H_2C = CH - O$$

$$CF_3$$

$$C - OBu - t$$

$$O$$

ANSWER 3 OF 5 CAPLUS COPYRIGHT 2006 ACS on STN L9

2004:631975 CAPLUS AN

141:181966 DN

Proton-neutralizing agent and photoresist containing the same TI

Kuzuha, Noboru IN

Aibaitsu K. K., Japan PA

Jpn. Kokai Tokkyo Koho, 10 pp. SO

CODEN: JKXXAF

Patent DT

Japanese LA

FAN. CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI PRAI	JP 2004217867 JP 2003-9721	A2	20040805	JP 2003-9721	20030117

The agent well neutralizes proton generated in dark during the storage of AB photoresist and is inert under exposure of the resist.

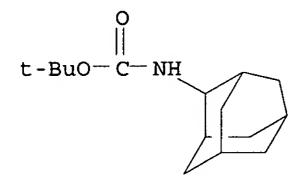
733037-96-2P IT

> RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(proton-neutralizing agent and photoresist containing the same)

733037-96-2 CAPLUS RN

Carbamic acid, tricyclo[3.3.1.13,7]dec-2-yl-, 1,1-dimethylethyl ester CN (9CI) (CA INDEX NAME)



ANSWER 4 OF 5 CAPLUS COPYRIGHT 2006 ACS on STN L9

2004:219910 CAPLUS AN

140:278422 DN

Chemical amplification type resist composition TI

Takata, Yoshiyuki; Yoshida, Isao; Nakanishi, Hirotoshi IN

Sumitomo Chemical Company, Limited, Japan PA

U.S. Pat. Appl. Publ., 22 pp. SO

CODEN: USXXCO

DT LA	CODEN: USXXCO Patent English			~>>	PP.D.		
FAN.CNT 1							
	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE		
PI	US 2004053171	A1	20040318	US 2003-657149	20030909		
	CN 1488996	A	20040414	CN 2003-156561	20030909		
	JP 2004126572	A2	20040422	JP 2003-319438	20030911		
PRAI	JP 2002-266539	A	20020912				

MARPAT 140:278422 OS

The present invention provides a chemical amplification type pos. resist ABcomposition comprising (1) a nitrogen containing compound of the formula A(-X-N(R13)C(=0)R14)n or A(-X-C(=0)N(R15)R16)n (A = alicyclic hydrocaron group; X = C1-4 alkylene, single bond; R13-16 = H, C1-12 alkyl, C3-12 cycloalkyl, C1-12 haloalkyl, etc.; n = 1-5); (2) resin which contains a structural unit having an acid labile group and which itself is insol. or poorly soluble in an alkali aqueous solution but becomes soluble in an alkali aqueous solution

by the action of an acid; and (3) an acid generator of the formula I (Q1-5

=H, hydroxyl, C1-12 alkyl, alkoxy; Z+ = II (P1-3 = H, hydroxyl, C1-6 allyl
and alkoxy), III (P4,5 = H, hydroxyl, C1-6 allyl and alkoxy),
P6P7S+-CH(P8)C(=0)P9 (P6,7 = C1-6 alkyl, C3-10 cycloalkyl, etc.; P8 = H;
P9 = C1-6 alkyl, C3-10 cycloalkyl, aromatic group, etc.)).

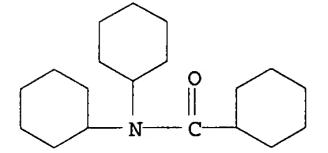
IT 550309-32-5P

RL: SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(chemical amplification type resist composition containing)

RN 550309-32-5 CAPLUS

CN Cyclohexanecarboxamide, N, N-dicyclohexyl- (9CI) (CA INDEX NAME)



L9 ANSWER 5 OF 5 CAPLUS COPYRIGHT 2006 ACS on STN

AN 2003:671498 CAPLUS

DN 139:188320

TI Positive photoresists showing superior transparency to 157-nm light and excellent sensitivity

IN Sasaki, Tomoya; Mizutani, Kazuyoshi; Kanna, Shinichi

PA Fuji Photo Film Co., Ltd., Japan

SO Jpn. Kokai Tokkyo Koho, 46 pp.

CODEN: JKXXAF

DT Patent

LA Japanese

FAN.CNT 1

PATENT NO. KIND DATE APPLICATION NO. DATE

PI JP 2003241381 A2 20030827 JP 2002-46284 20020222

PRAI JP 2002-46284 20020222

The photoresists, useful for F2 excimer laser lithog., comprise (A) resins increasing alkali solubility upon acid action and having repeating unit CR1R2CR3(L1XNHR4) (R1-R3 = H, Cl, CN, Me, F, fluoroalkyl, where ≥1 of them is F or fluoroalkyl; L1 = single bond, bivalent bridging group; X = CO, SO2; R4 = monovalent organic group) and (B) radiation-sensitive acid generators.

IT 581804-50-4P 581804-51-5P

RL: IMF (Industrial manufacture); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(binders; chemical amplified pos. photoresists containing fluoro-containing acid-labile binders showing high transparency to 157-nm light)

RN 581804-50-4 CAPLUS

CN 2-Propenamide, 2-fluoro-N-tricyclo[3.3.1.13,7]dec-2-yl-, polymer with 1-(1,1-dimethylethoxy)-4-ethenylbenzene (9CI) (CA INDEX NAME)

CM 1

CRN 581804-48-0 CMF C13 H18 F N O

CM 2

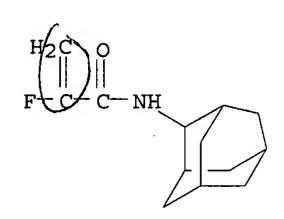
CRN 95418-58-9 CMF C12 H16 O

RN 581804-51-5 CAPLUS

CN 2-Propenamide, 2-fluoro-N-tricyclo[3.3.1.13,7]dec-2-yl-, polymer with
1-cyclohexyl-4-[2-[1-(4-ethenylphenoxy)ethoxy]ethoxy]benzene (9CI) (CAINDEX NAME)

CM 1

CRN 581804-48-0 CMF C13 H18 F N O



CM 2

CRN 326591-95-1 CMF C24 H30 O3

IT 581804-48-0P

RL: IMF (Industrial manufacture); RCT (Reactant); PREP (Preparation); RACT (Reactant or reagent)

(chemical amplified pos. photoresists containing fluoro-containing acid-labile

binders showing high transparency to 157-nm light)

RN 581804-48-0 CAPLUS

CN 2-Propenamide, 2-fluoro-N-tricyclo[3.3.1.13,7]dec-2-yl- (9CI) (CA INDEX NAME)

H2C O C-NH

=>

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2005:135411 CAPLUS
AN
     142:219688
DN
     Cyclic dithiocarbonates, their preparation and applications
TI
     Motokucho, Suguru; Sudo, Atsushi; Endo, Takeshi; Itagaki, Yoshiteru;
IN
     Kaneko, Ryosuke; Uenishi, Kazuya; Karim, Sikder Mohammad Abdul
     Henkel Kommanditgesellschaft Auf Aktien, Germany
PA
     Eur. Pat. Appl., 22 pp.
SO
     CODEN: EPXXDW
DT
     Patent
     English
LA
FAN.CNT 1
                         KIND
                                            APPLICATION NO.
                                                                    DATE
     PATENT NO.
                                DATE
                          A1
                                            EP 2003-18503
                                                                    20030815
PI
     EP 1506964
                                20050216
         R: AT, BE, CH, DE, DK, ES, FR, GB, GR, IT, LI, LU, NL, SE, MC, PT,
             IE, SI, LT, LV, FI, RO, MK, CY, AL, TR, BG, CZ, EE, HU, SK
     WO 2005016908
                                20050224
                                            WO 2004-EP2655
                                                                    20040315
                          A1
            AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH,
             CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD,
             GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC,
             LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI,
             NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY,
             TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW
        RW: BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW, AM, AZ,
             BY, KG, KZ, MD, RU, TJ, TM, AT, BE, BG, CH, CY, CZ, DE, DK, EE,
             ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,
             SK, TR, BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN,
             TD, TG
                                20030815
PRAI EP 2003-18503
                          Α
     MARPAT 142:219688
OS
     The present invention relates to cyclic 5-membered ring dithiocarbonate
AB
     compds. of the general formula I, wherein R1, R2, and R3 are the same or
     different, each of which denotes hydrogen or a C1-4 straight-chain or
     branched alkyl. The invention further relates to a process for producing
     these compds. and a variety of products obtainable by reacting the title
     compds. such as monomers for polymers useful for coating, adhesive,
     sealing composition, photoresist, etc. Thus, silylating glycidol
     with trimethylsilyl chloride gave glycidyl trimethylsilyl ether (II).
     Reacting II with CS2 in the presence of LiBr in THF gave a dithiocarbonate
     having silyl ether which was desilylated to give 5-hydroxymethyl-1,3-
     oxathiolane-2-thione (III). Reacting III with piperazine and subsequently
     oxidatively polymerizing the adduct gave a disulfide-containing thio urethane
     polymer having OH groups which could be further modified, e.g., by
     acetylation.
     843641-80-5DP, reaction products with epoxy resins and
{	t IT}
     crosslinkers
     RL: IMF (Industrial manufacture); PRP (Properties); TEM (Technical or
     engineered material use); PREP (Preparation); USES (Uses)
        (manufacture of cyclic dithiocarbonates useful for monomers and their
        applications)
     843641-80-5 CAPLUS
RN
    Carbamic acid, [1,3-cyclohexanediylbis(methylene)]bis-,
CN
    bis[(2-thioxo-1,3-oxathiolan-5-yl)methyl] ester (9CI) (CA INDEX NAME)
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ANSWER 1 OF 1 CAPLUS

**L8**·

$$\begin{array}{c} S \\ \\ S \\ \end{array} \begin{array}{c} O \\ \\ CH_2 - O - C - NH - CH_2 \\ \end{array} \begin{array}{c} O \\ \\ CH_2 - NH - C - O - CH_2 \\ \end{array} \begin{array}{c} O \\ \\ S \\ \end{array} \begin{array}{c} S \\ \end{array}$$